Supporting information

**Synthesis and optoelectronic properties of reduced graphene oxide/InP quantum dot hybrids**

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Figure S1

![Figure S1](image1.png)

**Figure S1.** High resolution P\(_{2p}\) XPS spectrum of the rGO/InP QD hybrids

Figure S2

![Figure S2](image2.png)

**Figure S2.** The current response of pure InP QDs versus time under intermittent blue light irradiation with a voltage of 1 V.